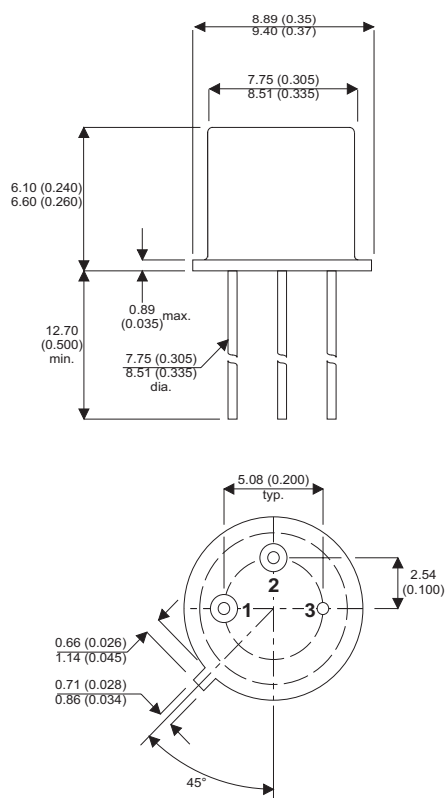


MECHANICAL DATA

Dimensions in mm (inches)



**SILICON EPITAXIAL
NPN TRANSISTOR**

FEATURES

General purpose power transistor for switching and linear applications in a hermetic TO-39 package.

TO-39 PACKAGE

PIN 1 – Emitter PIN 2 – Base PIN 3 – Collector

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise stated)

V_{CBO}	Collector – Base Voltage		900V
V_{CER}	Collector – Emitter Voltage	$R = 10\Omega$	900V
V_{EBO}	Emitter – Base Reverse Voltage		5V
I_C	Continuous Collector Current		2W
P_{TOT}	Total Device Dissipation	$T_C = 25^\circ\text{C}$	3.5A
T_J	Maximum Operating Junction Temperature		200°C
T_{STG}	and Storage Temperature Range		-55 to 200°C

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{CBO}	$V_{CB} = 900V$			0.012	mA
hFE	$V_{CE} = 10V$ $I_C = 0.02A$	20		180	—
fae			20		MHz